

DOUT3 1

DOUT2 3

ROUT2 5

RIN2 4

DIN2 6

DIN1 7

ROUT1 8

RIN1

C1-

GND 10

V_{CC} [11

C1+ 12

V+ 13

14

9

DB OR DW PACKAGE

(TOP VIEW)

28

27

Π DOUT4

RIN3

26 🛛 ROUT3

25 SHDN

24 EN

23 RIN4

21 DIN4

20 DIN3

18 RIN5

17 V_

16 C2-

C2+

15

22 ROUT4

19 ROUT5

FEATURES

- RS-232 Bus-Pin ESD Protection Exceeds ±15 kV Using Human-Body Model (HBM)
- Meets or Exceeds the Requirements of TIA/EIA-232-F and ITU v.28 Standards
- Operates at 5-V V_{CC} Supply
- Four Drivers and Five Receivers
- Operates up to 120 kbit/s
- Low Supply Current in Shutdown Mode . . . 1 μA Typical
- External Capacitors . . . 4 × 0.1 μF
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II

APPLICATIONS

- Battery-Powered Systems
- PDAs
- Notebooks
- Laptops
- Palmtop PCs
- Hand-Held Equipment

DESCRIPTION/ORDERING INFORMATION

The TRS211 device consists of four line drivers, five line receivers, and a dual charge-pump circuit with \pm 15-kV ESD protection pin to pin (serial-port connection pins, including GND). The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 5-V supply. The devices operate at data signaling rates up to 120 kbit/s and a maximum of 30-V/µs driver output slew rate.

The TRS211 has both shutdown (SHDN) and enable control (\overline{EN}). In shutdown mode, the charge pumps are turned off, V+ is pulled down to V_{CC}, V– is pulled to GND, and the transmitter outputs are disabled. This reduces supply current typically to 1 μ A. \overline{EN} is used to put the receiver outputs into the high-impedance state to allow wired-OR connection of two RS-232 ports. It has no effect on the RS-232 drivers or the charge pumps.

T _A	PA	CKAGE ⁽¹⁾⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING	
	SOIC – DW	Tube of 20	TRS211CDW	TD00110	
0°C to 70°C	50IC - DW	Reel of 1000	TRS211CDWR	- TRS211C	
		Tube of 50	TRS211CDB	TROMAC	
	SSOP – DB	Reel of 2000	TRS211CDBR	TRS211C	
		Tube of 20	TRS211IDW	TDC0441	
4000 to 0500	SOIC – DW	Reel of 1000	TRS211IDWR	- TRS211I	
–40°C to 85°C		Tube of 50	TRS211IDB	TD00441	
	SSOP – DB	Reel of 2000	TRS211IDBR	- TRS211I	

ORDERING INFORMATION

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

(2) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.



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TRS211 5-V MULTICHANNEL RS-232 LINE DRIVER/RECEIVER WITH \pm 15-kV ESD PROTECTION $_{\rm SLLS811-JULY\ 2007}$



FUNCTION TABLES⁽¹⁾

INPU	JTS		DECENTED	DEVICE STATUS
SHDN	EN	DRIVER RECEIVER D		DEVICE STATUS
L	L	All active	All active	Normal operation
L	Н	All active	Z	Normal operation
н	х	Z	Z	Shutdown

(1) X = don't care, Z = high impedance

Each Driver⁽¹⁾

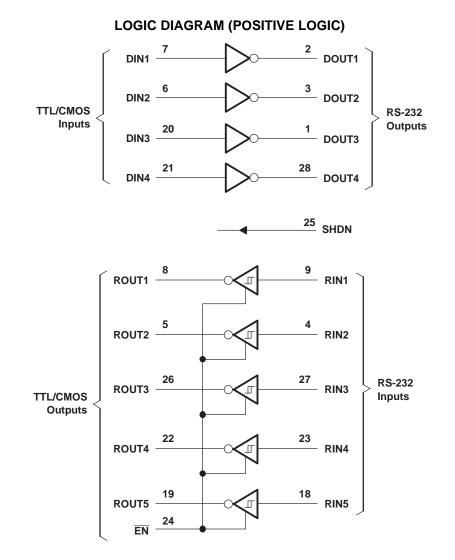
INF	UTS	OUTPUT	DRIVER STATUS
DIN	SHDN	DOUT	DRIVER STATUS
L	L	Н	Normal aparation
н	L	L	Normal operation
Х	Н	Z	Powered off

(1) X = don't care, Z = high impedance

Each Receiver⁽¹⁾

INP	UTS	OUTPUT	RECEIVER STATUS
RIN	EN	ROUT	RECEIVER STATUS
L	L	Н	Normal anaration
н	L	L	Normal operation
Х	Н	Z	Powered off

(1) X = don't care, Z = high impedance



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Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range ⁽²⁾		-0.3	6	V
V+	Positive charge pump voltage range ⁽²⁾		V _{CC} – 0.3	14	V
V–	Negative charge pump voltage range ⁽²⁾		0.3	-14	V
V		Drivers	-0.3	V+ + 0.3	V
VI	Input voltage range	Receivers		±30	v
V		Drivers	V0.3	V+ + 0.3	V
Vo	Output voltage range Receivers		-0.3	V _{CC} + 0.3	v
	Short-circuit duration	DOUT		Continuous	
0	Package thermal impedance ⁽³⁾⁽⁴⁾	DB package		62	°C/W
θ_{JA}	Fackage thermal impedance (77)	DW package		46	C/W
TJ	Operating virtual junction temperature			150	°C
T _{stg}	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltages are with respect to network GND.

(3) Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.

(4) The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions⁽¹⁾

See Figure 6

			MIN	NOM	MAX	UNIT
	Supply voltage		4.5	5	5.5	V
V _{IH}	Driver high-level input voltage	DIN	2			V
	Control high-level input voltage	EN, SHDN	2.4			V
VIL	Driver and control low-level input voltage	DIN, EN, SHDN			0.8	V
V	Driver and control input voltage	DIN, EN, SHDN	0		5.5	V
VI	Receiver input voltage		-30		30	V
т	Operating free air temperature	TRS211C	0		70	°C
T _A	Operating free-air temperature	TRS211I	-40		85	÷ل

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 5 V \pm 0.5 V.

Electrical Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST	TEST CONDITIONS		TYP ⁽²⁾	MAX	UNIT
I _{CC}	Supply current	No load,	See Figure 6		14	20	mA
	Shutdown supply current	$T_A = 25^{\circ}C$,	See Figure 1		1	10	μA

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 5 V ± 0.5 V.

(2) All typical values are at $V_{CC} = 5$ V, and $T_A = 25^{\circ}C$.

DRIVER SECTION

Electrical Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 4)

	PARAMETER	TEST COND	ITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V _{OH}	High-level output voltage	All DOUT at $R_L = 3 \text{ k}\Omega$ to Ω	GND	5	9		V
V _{OL}	Low-level output voltage	All DOUT at $R_L = 3 \text{ k}\Omega$ to Ω	All DOUT at $R_L = 3 \text{ k}\Omega$ to GND		-9		V
	Driver high-level input current	-level input current DIN = V _{CC}			15	200	
Чн	Control high-level input current	$\overline{\text{EN}}$, SHDN = V _{CC}	\overline{EN} , SHDN = V _{CC}		3	10	μA
	Driver low-level input current	DIN = 0 V	DIN = 0 V		-15	-200	۵
IIL	Control low-level input current	EN, SHDN = 0 V			-3	-10	μA
I _{OS}	Short-circuit output current ⁽³⁾	V _{CC} = 5.5 V,	$V_{O} = 0 V$		±10	±60	mA
r _o	Output resistance	V_{CC} , V+, and V- = 0 V,	$V_0 = \pm 2 V$	300			Ω

(1) Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 5 V ± 0.5 V.

(2) All typical values are at $V_{CC} = 5$ V, and $T_A = 25^{\circ}C$.

(3) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

Switching Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CON	DITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
	Maximum data rate	$C_L = 50 \text{ pF}$ to 1000 pF, One DOUT switching,	$R_L = 3 k\Omega$ to 7 k Ω , See Figure 2	120			kbit/s
t _{PLH(D)}	Propagation delay time, low- to high-level output	$C_L = 2500 \text{ pF},$ All drivers loaded,	$R_L = 3 k\Omega$, See Figure 2		2		μs
t _{PHL(D)}	Propagation delay time, high- to low-level output	C _L = 2500 pF, All drivers loaded,	$R_L = 3 k\Omega$, See Figure 2		2		μs
t _{sk(p)}	Pulse skew ⁽³⁾	C_L = 150 pF to 2500 pF, See Figure 3	$R_L = 3 k\Omega \text{ to } 7 k\Omega,$		300		ns
SR(tr)	Slew rate, transition region	$C_L = 50 \text{ pF to } 1000 \text{ pF},$ $V_{CC} = 5 \text{ V}$	$R_L = 3 \ k\Omega \ to \ 7 \ k\Omega$,	3	6	30	V/µs

(1) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 5 V \pm 0.5 V.

(2) All typical values are at $V_{CC} = 5$ V, and $T_A = 25^{\circ}C$.

(3) Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.

ESD Protection

PIN	TEST CONDITIONS	TYP	UNIT
DOUT, RIN	Human-Body Model	±15	kV

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RECEIVER SECTION

Electrical Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 6)

	PARAMETER	TEST	T CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V _{OH}	High-level output voltage	$I_{OH} = -1 \text{ mA}$		3.5	$V_{CC} - 0.4$		V
V _{OL}	Low-level output voltage	I _{OH} = 1.6 mA				0.4	V
V _{IT+}	Positive-going input threshold voltage	$V_{CC} = 5 V$,	$T_A = 25^{\circ}C$		1.7	2.4	V
V _{IT-}	Negative-going input threshold voltage	V _{CC} = 5 V,	$T_A = 25^{\circ}C$	0.8	1.2		V
V _{hys}	Input hysteresis ($V_{IT+} - V_{IT-}$)			0.2	0.5	1	V
r _i	Input resistance	V _{CC} = 5 V,	$T_A = 25^{\circ}C$	3	5	7	kΩ
	Output leakage current	$\overline{EN} = V_{CC},$	$0 \le \text{ROUT} \le \text{V}_{\text{CC}}$		±0.05	±10	μa

Switching Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER		ONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
t _{PLH(R)}	Propagation delay time, low- to high-level output	C _L = 150 pF,	See Figure 4		0.5	10	μs
t _{PHL(R)}	Propagation delay time, high- to low-level output	C _L = 150 pF,	See Figure 4		0.5	10	μs
t _{en}	Output enable time	C _L = 150 pF, See Figure 5	$R_L = 1 \ k\Omega$,		600		ns
t _{dis}	Output disable time	C _L = 150 pF, See Figure 5	$R_L = 1 \ k\Omega$,		200		ns
t _{sk(p)}	Pulse skew ⁽³⁾	See Figure 3			300		ns

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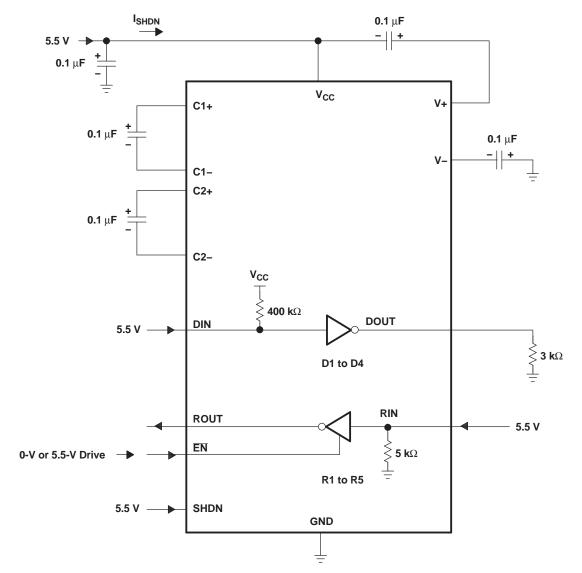
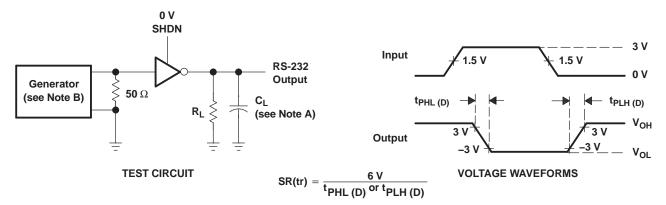


Figure 1. Shutdown Current Test Circuit

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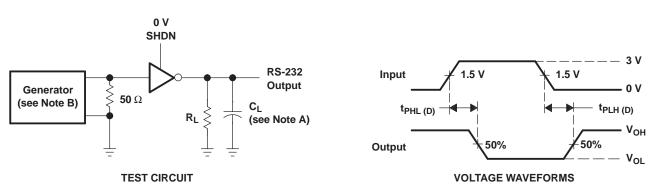


PARAMETER MEASUREMENT INFORMATION (continued)



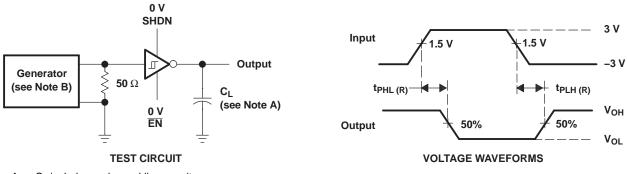
- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 120 kbit/s, $Z_0 = 50 \Omega$, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 2. Driver Slew Rate and Propagation Delay Times



- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 120 kbit/s, Z_0 = 50 Ω , 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 3. Driver Pulse Skew



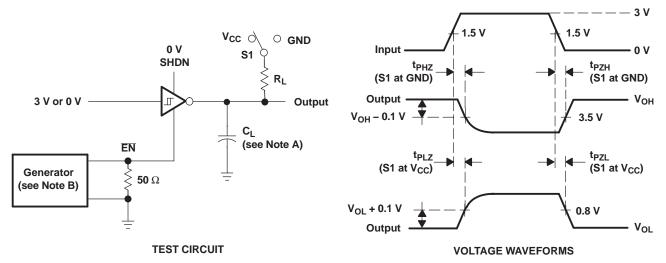
- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: $Z_O = 50 \ \Omega$, 50% duty cycle, $t_r \le 10 \text{ ns}$, $t_f \le 10 \text{ ns}$.

Figure 4. Receiver Propagation Delay Times



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PARAMETER MEASUREMENT INFORMATION (continued)



- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: $Z_0 = 50 \Omega$, 50% duty cycle, $t_r \le 10 \text{ ns}$, $t_f \le 10 \text{ ns}$.
- $C. \quad t_{PLZ} \text{ and } t_{PHZ} \text{ are the same as } t_{dis}.$
- D. t_{PZL} and t_{PZH} are the same as t_{en} .

Figure 5. Receiver Enable and Disable Times

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28 DOUT4 DOUT3 2 27 DOUT1 RIN3 5 kΩ 3 DOUT2 4 RIN2 26 **ROUT3** $\mathbf{5} \mathbf{k} \Omega$ 25 SHDN 24 5 EN ROUT2 23 RIN4 5 V 5 **k**Ω **400 k**Ω 6 22 DIN2 -**ROUT4** 5 V 5 V **400 k**Ω 7 DIN1 ≶ **400 k**Ω 21 8 DIN4 ROUT1 9 5 V RIN1 Π GND 10 ≶ **400 k**Ω 20 DIN3 CBYPASS **= 0.1** μF + 19 11 **ROUT5** v_{cc} Vcc C3†= 18 RIN5 **0.1** μF + 12 5 **k**Ω C1+ 6.3 V C4 = 13 0.1 μF V+ 16 V 17 v-C1 = ÷ **0.1** μ**F** 14 C1-16 6.3 V C2-C2 = 0.1 μF ÷ 16 V 15 C2+

APPLICATION INFORMATION

 † C3 can be connected to V_CC or GND.

- A. Resistor values shown are nominal.
- B. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

Figure 6. Typical Operating Circuit and Capacitor Values

APPLICATION INFORMATION (continued)

Capacitor Selection

The capacitor type used for C1–C4 is not critical for proper operation. The TRS211 requires 0.1- μ F capacitors, although capacitors up to 10 μ F can be used without harm. Ceramic dielectrics are suggested for the 0.1- μ F capacitors. When using the minimum recommended capacitor values, make sure the capacitance value does not degrade excessively as the operating temperature varies. If in doubt, use capacitors with a larger (e.g., 2×) nominal value. The capacitors' effective series resistance (ESR), which usually rises at low temperatures, influences the amount of ripple on V+ and V–.

Use larger capacitors (up to 10 μ F) to reduce the output impedance at V+ and V–.

Bypass V_{CC} to ground with at least 0.1 μ F. In applications sensitive to power-supply noise generated by the charge pumps, decouple V_{CC} to ground with a capacitor the same size as (or larger than) the charge-pump capacitors (C1–C4).

Electrostatic Discharge (ESD) Protection

TI TRS211 devices have standard ESD protection structures incorporated on the pins to protect against electrostatic discharges encountered during assembly and handling. In addition, the RS232 bus pins (driver outputs and receiver inputs) of these devices have an extra level of ESD protection. Advanced ESD structures were designed to successfully protect these bus pins against ESD discharge of \pm 15 kV when powered down.

ESD Test Conditions

ESD testing is stringently performed by TI, based on various conditions and procedures. Please contact TI for a reliability report that documents test setup, methodology, and results.

Human-Body Model (HBM)

The HBM of ESD testing is shown in Figure 7. Figure 8 shows the current waveform that is generated during a discharge into a low impedance. The model consists of a 100-pF capacitor charged to the ESD voltage of concern and subsequently discharged into the DUT through a 1.5-k Ω resistor.

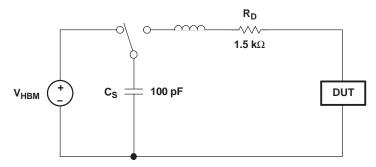


Figure 7. HBM ESD Test Circuit

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APPLICATION INFORMATION (continued)

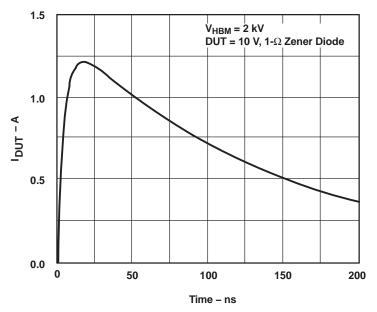


Figure 8. Typical HBM Current Waveform

Machine Model (MM)

The MM ESD test applies to all pins, using a 200-pF capacitor with no discharge resistance. The purpose of the MM test is to simulate possible ESD conditions that can occur during the handling and assembly processes of manufacturing. In this case, ESD protection is required for all pins, not just RS-232 pins. However, after PC board assembly, the MM test no longer is as pertinent to the RS-232 pins.



10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TRS211CDB	ACTIVE	SSOP	DB	28	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	TRS211C	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <= 1000ppm threshold. Antimony trioxide based flame retardants must also meet the <= 1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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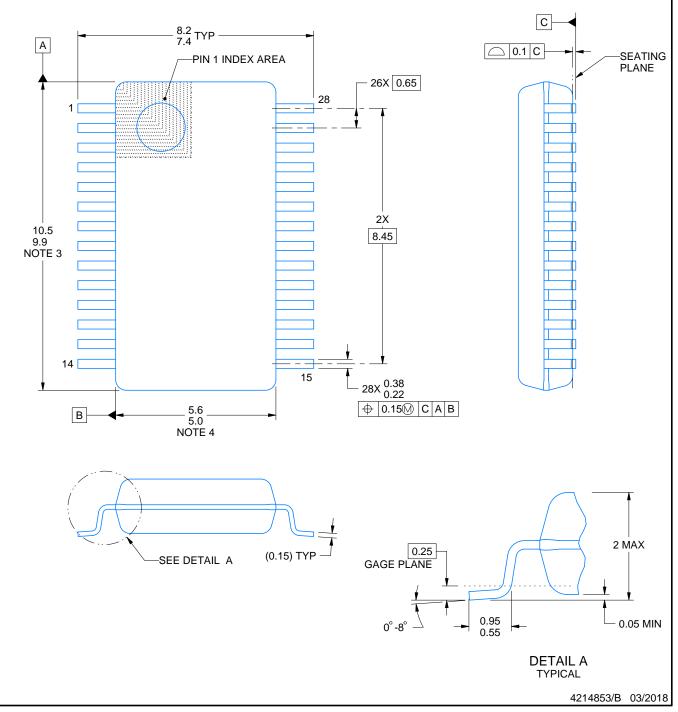
DB0028A



PACKAGE OUTLINE

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.



DB0028A

EXAMPLE BOARD LAYOUT

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DB0028A

EXAMPLE STENCIL DESIGN

SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



DW (R-PDSO-G28)

PLASTIC SMALL OUTLINE



NOTES:

A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-013 variation AE.



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